

# Hieu Pham Trung Nguyen

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

62

papers

1,953

citations

21

h-index

43

g-index

78

ext. papers

2,233

ext. citations

4.1

avg, IF

4.75

L-index

#	Paper	IF	Citations
62	Polarization-Engineered p-Type Electron-Blocking-Layer-Free III-Nitride Deep-Ultraviolet Light-Emitting Diodes for Enhanced Carrier Transport. <i>Journal of Electronic Materials</i> , <b>2022</b> , 51, 838-846	1.9	0
61	Controlled carrier mean free path for the enhanced efficiency of III-nitride deep-ultraviolet light-emitting diodes. <i>Applied Optics</i> , <b>2021</b> , 60, 3088-3093	1.7	1
60	Enhancing Efficiency of AlGaIn Ultraviolet-B Light-Emitting Diodes with Graded p-AlGaIn Hole Injection Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2021</b> , 218, 2100003	1.6	1
59	Epitaxial Growth and Characterization of AlInN-Based Core-Shell Nanowire Light Emitting Diodes Operating in the Ultraviolet Spectrum. <i>Scientific Reports</i> , <b>2020</b> , 10, 2547	4.9	13
58	Improving carrier transport in AlGaIn deep-ultraviolet light-emitting diodes using a strip-in-a-barrier structure. <i>Applied Optics</i> , <b>2020</b> , 59, 5276-5281	1.7	11
57	High-performance nanowire ultraviolet light-emitting diodes with potassium hydroxide and ammonium sulfide surface passivation. <i>Applied Optics</i> , <b>2020</b> , 59, 7352-7356	1.7	5
56	Enhanced hole transport in AlGaIn deep ultraviolet light-emitting diodes using a double-sided step graded superlattice electron blocking layer. <i>Journal of the Optical Society of America B: Optical Physics</i> , <b>2020</b> , 37, 2564	1.7	5
55	High performance electron blocking layer-free InGaIn/GaN nanowire white-light-emitting diodes. <i>Optics Express</i> , <b>2020</b> , 28, 665-675	3.3	15
54	Enhancing the light extraction efficiency of AlInN nanowire ultraviolet light-emitting diodes with photonic crystal structures. <i>Optics Express</i> , <b>2020</b> , 28, 22908-22918	3.3	9
53	Deep red fluoride dots-in-nanoparticles for high color quality micro white light-emitting diodes. <i>Optics Express</i> , <b>2020</b> , 28, 26189-26199	3.3	7
52	High-performance electron-blocking-layer-free deep ultraviolet light-emitting diodes implementing a strip-in-a-barrier structure. <i>Optics Letters</i> , <b>2020</b> , 45, 5125-5128	3	4
51	Numerical investigation on the device performance of electron blocking layer free AlInN nanowire deep ultraviolet light-emitting diodes. <i>Optical Materials Express</i> , <b>2020</b> , 10, 472	2.6	8
50	Single and double-gate based AlGaIn/GaN MOS-HEMTs for the design of low-noise amplifiers: a comparative study. <i>IET Circuits, Devices and Systems</i> , <b>2020</b> , 14, 1018-1025	1.1	1
49	Full-Color InGaIn/AlGaIn Nanowire Micro Light-Emitting Diodes Grown by Molecular Beam Epitaxy: A Promising Candidate for Next Generation Micro Displays. <i>Micromachines</i> , <b>2019</b> , 10,	3.3	22
48	Full-Color III-Nitride Nanowire Light-Emitting Diodes <b>2019</b> , 3, 551		5
47	Observation of Fano-like resonance in dual-blade shaped gold nanostructures. <i>Journal Physics D: Applied Physics</i> , <b>2019</b> , 52, 045106	3	3
46	Enhanced Efficiency of Dye-Sensitized Solar Cells Based on Polyol-Synthesized Nickel/Zinc Oxide Composites. <i>Journal of Electronic Materials</i> , <b>2019</b> , 48, 252-260	1.9	2

45	Photonic crystal-based permutation switch for optical networks. <i>Photonic Network Communications</i> , <b>2018</b> , 35, 90-96	1.7	7
44	Effects of optical absorption in deep ultraviolet nanowire light-emitting diodes. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , <b>2018</b> , 28, 106-110	2.6	7
43	Controlling Fano resonances in multilayer dielectric gratings towards optical bistable devices. <i>Scientific Reports</i> , <b>2018</b> , 8, 16404	4.9	6
42	Polyol Synthesis of Zinc Oxide-Graphene Composites: Enhanced Dye- Sensitized Solar Cell Efficiency. <i>Current Nanomaterials</i> , <b>2018</b> , 3, 52-60	1.3	6
41	Controlling color emission of InGaN/AlGaIn nanowire light-emitting diodes grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2017</b> , 35, 02B108	1.3	14
40	Fabrication of Phosphor-Free III-Nitride Nanowire Light-Emitting Diodes on Metal Substrates for Flexible Photonics. <i>ACS Omega</i> , <b>2017</b> , 2, 5708-5714	3.9	9
39	High efficiency green/yellow and red InGaN/AlGaIn nanowire light-emitting diodes grown by molecular beam epitaxy. <i>Journal of Science: Advanced Materials and Devices</i> , <b>2017</b> , 2, 150-155	4.2	21
38	4-Port reciprocal optical circulators employing photonic crystals for integrated photonics circuits. <i>Optik</i> , <b>2017</b> , 144, 586-590	2.5	5
37	Correlative Nanoscale Luminescence and Elemental Mapping in InGaN/(Al)GaIn Dot-in-a-wire Heterostructures <b>2016</b> , 815-816		
36	Tunable, full-color nanowire light emitting diode arrays monolithically integrated on Si and sapphire <b>2016</b> ,		10
35	Fano-induced spontaneous emission enhancement of molecule placed in a cluster of asymmetrically-arranged metallic nanoparticles. <i>Journal of Luminescence</i> , <b>2016</b> , 173, 199-202	3.8	5
34	Experimental and numerical optical characterization of plasmonic copper nanoparticles embedded in ZnO fabricated by ion implantation and annealing. <i>Journal of Alloys and Compounds</i> , <b>2016</b> , 669, 246-253 <sup>57</sup>		8
33	Atomic-Scale Compositional Fluctuations in Ternary III-Nitride Nanowires <b>2016</b> , 550-551		
32	Nanostructured Optoelectronics: Materials and Devices. <i>Journal of Nanomaterials</i> , <b>2016</b> , 2016, 1-2	3.2	4
31	InGaN/GaN dot-in-a-wire: ultimate terahertz nanostructure. <i>Laser and Photonics Reviews</i> , <b>2015</b> , 9, 105-118 <sup>3</sup>		2
30	High-power phosphor-free InGaN/AlGaIn dot-in-a-wire core-shell white light-emitting diodes <b>2015</b> ,		1
29	Alternating-Current InGaN/GaN Tunnel Junction Nanowire White-Light Emitting Diodes. <i>Nano Letters</i> , <b>2015</b> , 15, 6696-701	11.5	64
28	Atomic Ordering in InGaN Alloys within Nanowire Heterostructures. <i>Nano Letters</i> , <b>2015</b> , 15, 6413-8	11.5	30

27	Interplay of strain and indium incorporation in InGaN/GaN dot-in-a-wire nanostructures by scanning transmission electron microscopy. <i>Nanotechnology</i> , <b>2015</b> , 26, 344002	3.4	19
26	III-Nitride nanowire optoelectronics. <i>Progress in Quantum Electronics</i> , <b>2015</b> , 44, 14-68	9.1	152
25	Engineering the carrier dynamics of InGaN nanowire white light-emitting diodes by distributed p-AlGaN electron blocking layers. <i>Scientific Reports</i> , <b>2015</b> , 5, 7744	4.9	74
24	Phosphor-Free InGaN/GaN Dot-in-a-Wire White Light-Emitting Diodes on Copper Substrates. <i>Journal of Electronic Materials</i> , <b>2014</b> , 43, 868-872	1.9	15
23	. <i>IEEE Journal of Quantum Electronics</i> , <b>2014</b> , 50, 483-490	2	29
22	p-Type dopant incorporation and surface charge properties of catalyst-free GaN nanowires revealed by micro-Raman scattering and X-ray photoelectron spectroscopy. <i>Nanoscale</i> , <b>2014</b> , 6, 9970-6	7.7	21
21	Engineering the color rendering index of phosphor-free InGaN/(Al)GaN nanowire white light emitting diodes grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2014</b> , 32, 02C113	1.3	10
20	Color-tunable, phosphor-free InGaN nanowire light-emitting diode arrays monolithically integrated on silicon. <i>Optics Express</i> , <b>2014</b> , 22 Suppl 7, A1768-75	3.3	69
19	Improvement of the emission properties from InGaN/GaN dot-in-a-wire nanostructures after treatment in the flowing afterglow of a microwave N <sub>2</sub> plasma. <i>Nanotechnology</i> , <b>2014</b> , 25, 435606	3.4	8
18	Molecular beam epitaxial growth and characterization of InGaN/GaN dot-in-a-wire nanoscale heterostructures: toward ultrahigh efficiency phosphor-free white light emitting diodes <b>2013</b> ,		2
17	One-step overall water splitting under visible light using multiband InGaN/GaN nanowire heterostructures. <i>ACS Nano</i> , <b>2013</b> , 7, 7886-93	16.7	162
16	Highly stable photoelectrochemical water splitting and hydrogen generation using a double-band InGaN/GaN core/shell nanowire photoanode. <i>Nano Letters</i> , <b>2013</b> , 13, 4356-61	11.5	157
15	Spectral and spatial contributions to white light generation from InGaN/GaN dot-in-a-wire nanostructures. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 164305	2.5	3
14	High efficiency photoelectrochemical water splitting and hydrogen generation using GaN nanowire photoelectrode. <i>Nanotechnology</i> , <b>2013</b> , 24, 175401	3.4	70
13	Growth of large-scale vertically aligned GaN nanowires and their heterostructures with high uniformity on SiO(x) by catalyst-free molecular beam epitaxy. <i>Nanoscale</i> , <b>2013</b> , 5, 5283-7	7.7	75
12	Breaking the carrier injection bottleneck of phosphor-free nanowire white light-emitting diodes. <i>Nano Letters</i> , <b>2013</b> , 13, 5437-42	11.5	117
11	Highly efficient, spectrally pure 340 nm ultraviolet emission from Al <sub>x</sub> Ga <sub>1-x</sub> N nanowire based light emitting diodes. <i>Nanotechnology</i> , <b>2013</b> , 24, 345201	3.4	48
10	Optical phonon modes in InGaN/GaN dot-in-a-wire heterostructures grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 121901	3.4	1

9	On the efficiency droop of top-down etched InGaN/GaN nanorod light emitting diodes under optical pumping. <i>AIP Advances</i> , <b>2013</b> , 3, 082103	1.5	13
8	Controlling electron overflow in phosphor-free InGaN/GaN nanowire white light-emitting diodes. <i>Nano Letters</i> , <b>2012</b> , 12, 1317-23	11.5	157
7	Temperature-dependent nonradiative recombination processes in GaN-based nanowire white-light-emitting diodes on silicon. <i>Nanotechnology</i> , <b>2012</b> , 23, 194012	3.4	54
6	Preparing nano-hole arrays by using porous anodic aluminum oxide nano-structural masks for the enhanced emission from InGaN/GaN blue light-emitting diodes. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , <b>2012</b> , 3, 045018	1.6	2
5	High-Efficiency InGaN/GaN Dot-in-a-Wire Red Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , <b>2012</b> , 24, 321-323	2.2	30
4	p-Type modulation doped InGaN/GaN dot-in-a-wire white-light-emitting diodes monolithically grown on Si(111). <i>Nano Letters</i> , <b>2011</b> , 11, 1919-24	11.5	218
3	InN p-i-n Nanowire Solar Cells on Si. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2011</b> , 17, 1063-1069	3.8	57
2	Full-color InGaN/GaN dot-in-a-wire light emitting diodes on silicon. <i>Nanotechnology</i> , <b>2011</b> , 22, 445202	3.4	71
1	2DEG characteristics of InAlAs/InP based HEMTs by solving Schrödinger and Poisson equations followed by device characteristics. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , e2941	1	